Quantum quench of Kondo correlations in optical absorption

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The interaction between a single confined spin and the spins of an electron reservoir leads to one of the most remarkable phenomena of many-body physics—the Kondo effect1–2. Electronic transport measurements on single artificial atoms, or quantum dots, have made it possible to study the effect in great detail3–7. Here we report optical measurements on a single semiconductor quantum dot tunnel-coupled to a degenerate electron gas which show that absorption of a single photon leads to an abrupt change in the system Hamiltonian and a quantum quench of Kondo correlations. By inferring the characteristic power-law exponents from the experimental absorption line shapes, we find a unique signature of the quench in the form of an Anderson orthogonality catastrophe8,9, induced by a vanishing overlap between the initial and final many-body wavefunctions. We show that the power-law exponent that determines the degree of orthogonality can be tuned using an external magnetic field9, which unequivocally demonstrates that the observed absorption line shape originates from Kondo correlations. Our experiments demonstrate that optical measurements on single artificial atoms offer new perspectives on many-body phenomena previously studied using transport spectroscopy only.

Optical spectroscopy of single quantum dots has demonstrated its potential for applications in quantum information processing, particularly in the realization of single- and entangled-photon sources8,9, coherent spin qubits10,11 and a spin–photon interface12,13. Although recent experiments have established this system as a new model for solid-state quantum optics, all of the striking experimental observations made so far can be understood within the framework of single- or few-particle physics enriched by perturbative coupling to reservoirs involving phonons, a degenerate electron gas14,15,17,19, or nuclear spins16,19.

We present differential transmission experiments20 on single, charge-tunable quantum dots that reveal optical signatures of the Kondo effect. By contrast with prior experiments12,21, the tunnel coupling between the quantum dot and a nearby degenerate electron gas, which we refer to as the fermionic reservoir, is engineered to be so strong that the resulting exchange interactions cannot be treated using a perturbative system–reservoir theory: in the initial state, the ‘system’—quantum dot spin—is maximally entangled with the fermionic reservoir, forming a singlet. Various settings have been proposed for finding optical signatures of Kondo physics8,22–25; our work is most closely related to the theoretical investigation of refs 8, 25.

The feature that differentiates our results from all prior transport-based investigations of the Kondo effect8,9 is the realization of a quantum quench of the local Hamiltonian; in our experiments, photon absorption abruptly turns off the exchange interaction between the quantum dot electron and the fermionic reservoir, leading to the destruction of the correlated dot–reservoir singlet that otherwise acts as a local scattering potential for all reservoir electrons. The overlap between N-electron fermionic reservoir states with and without a local scattering potential scales as \( N^{-x} \), with \( x > 0 \) (refs 6, 7). This reduced overlap, called an Anderson orthogonality catastrophe (AOC), leads to a power-law tail in absorption if the scattering potential is turned on or off by photon absorption. Here we determine the AOC-induced power-law exponents in the absorption line shape that uniquely characterize the quench of Kondo correlations. Moreover, by tuning the applied laser frequency, we observe both the perturbative and the non-perturbative regimes of the Kondo effect in one absorption line shape, without having to change the fermionic reservoir (electron) temperature, \( T_{\text{F}} \). The AOC after a Kondo quench can, in principle, also be probed by core-level X-ray absorption spectroscopy of suitable bulk materials26, but optical studies of quantum dots offer higher resolution and a tunable local Hamiltonian.

The quantum dot sample we study is shown schematically in Fig. 1a: a gate voltage, \( V_g \), applied between a top Schottky gate and the degenerate electron gas, allows us to tune the charging state of the quantum dot27. Figure 1b shows the photoluminescence spectrum of a particular quantum dot (dot 1), as a function of \( V_g \), where different discrete ‘charging plateaux’ are clearly observable. The dependence of the photoluminescence energy on the quantum dot charging state originates from a Coulomb renormalization of the optical transition energy. In addition to photoluminescence lines (for example \( X^0 \)) associated with a fixed charging state (for example neutral) of the quantum dot, we also observe spatially indirect transitions with a strong dependence on \( V_g \) (refs 8, 17; see Fig. 1b, red arrow).

Figure 1 | Single quantum dot strongly coupled to a fermionic reservoir. a, Band structure of the device. The quantum dots are separated by a 15-nm tunnel barrier from an n++ - doped GaAs layer (fermionic reservoir). A voltage, \( V_g \), applied between the electron gas and a semi-transparent NiCr gate on the sample surface controls the relative value of the quantum dot single-particle energy levels with respect to the Fermi energy, \( E_F \). b, Low-temperature (4 K) photoluminescence spectrum of a single quantum dot (dot 1) as a function of \( V_g \). \( n_0 \) denotes the initial state electron occupancy of the quantum dot. The interaction of the quantum dot electron with the Fermi sea leads to a broadening of the photoluminescence lines at the plateau edges (yellow arrows) and indirect recombinations of a quantum dot hole and a Fermi sea electron (red arrow). Indirect transitions are identified by the stronger \( V_g \) dependence of the transition energy, compared with that for direct transitions. A detailed discussion of the origin of various photoluminescence lines can be found in ref. 17.

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In this Letter, we focus on the $X^-$ plateau, for which the quantum dot carries the charge of a single electron and the influence of the fermionic reservoir on the quantum dot photoluminescence dispersion and linewidth is strongest. The $X^-$ optical transition couples the initial configuration, containing on average one electron in the quantum dot, to a final configuration, containing on average two electrons and a valence-band hole (a negatively charged trion). This transition can be described within the framework of an excitonic Anderson model (EAM), depicted schematically in Fig. 2c (and described explicitly in Supplementary Information). It is parameterized by the energy, $\varepsilon$, of the quantum dot electron level with respect to the Fermi level; the on-site Coulomb repulsion, $U_{eh}$; the tunnelling rate, $J'$, between quantum dot and fermionic reservoir; the half-bandwidth, $D$, of the fermionic reservoir; and the electron–hole Coulomb attraction, $U_{eh}$. The last is relevant only in the final configuration, where it effectively lowers the electron level energy to $\varepsilon - U_{eh}$, thus ensuring the double occupancy of the electron level. An estimate from the photoluminescence data in Fig. 1b yields $U_{eh} \approx U_{ec} + 4 \text{ meV}$.

The inset of Fig. 2a shows high-resolution laser absorption spectroscopy on dot 1 across the $X^-$ single-electron charging plateau

$ΔE_{\text{resonance}} (\text{meV})$  

$\text{Occupation}$  

$\varepsilon/U_{\text{eh}}$  

$\text{Gate voltage (mV)}$  

$\text{Final state}$  

$\text{Initial state}$  

$\varepsilon + U_{eh} - U_{\text{ab}}$  

$\text{Peak contrast} (A/eV)$

Figure 2 | Gate voltage dependence of the peak absorption strength. a, Experimental data (symbols) for the $\varepsilon$ dependence of the shift in the resonance energy, $ΔE_{\text{resonance}}$ (blue, left axis), and the absorption contrast (red, right axis) are well reproduced by NRG calculations (solid lines) for the following parameters: $U_{eh} = 7.5 \text{ meV}, J' = 0.7 \text{ meV}, D = 3.5 \text{ meV}, U_{eh} = 11 \text{ meV}, T_{FB} = 180 \text{ mK}$. Inset, absorption on the negatively charged exciton $X^-$ transition of dot 1 as a function of the gate voltage, measured at $T_{FB} = 180 \text{ mK}$. NRG results for the respective occupations, $n_1$ and $n_2$, of the quantum dot electron level in the initial and final ground states. $\varepsilon$, Energy renormalization process: the initial configuration (left) features a single electron in the quantum dot, whose energy is lowered by virtual tunnelling between the dot and the fermionic reservoir. Because virtual excitations with energy $ΔE$ contribute a shift proportional to $-1/ΔE$, the total shift (involving a sum over all possible values of $ΔE$), is strongest near the edges of the $X^-$ plateau. Towards the right-hand edge ($\varepsilon$ near zero), the dominant contribution comes from virtual tunnelling of the quantum dot electron into the fermionic reservoir (as depicted); towards the left-hand edge ($\varepsilon$ near $-U_{eh}$), it comes from virtual tunnelling of a fermionic reservoir electron into the quantum dot (not depicted). In the final configuration (right), the quantum dot contains two electrons and a hole. The electron–hole Coulomb attraction, $U_{eh}$, effectively lowers the quantum dot electron level energy to $\varepsilon - U_{eh}$. This raises the energy cost, $ΔE$, for virtual excitations by $U_{eh} - U_{\text{ab}}$, which is $>J'$, such that the final-state energy renormalization is negligible. The renormalization of the transition energy, probed by a weak laser, is thus mainly due to initial-state energy renormalization. d, Anderson orthogonality: the Kondo cloud (left-hand diagram) and local singlet (right-hand diagram) of the initial and final configurations produce strong or weak scattering phase shifts, respectively.

$A(\varepsilon) = A(\varepsilon_{\text{max}})$ for dot 1, plotted versus the laser detuning, $ν$, on a log–log scale. Here $\varepsilon_{\text{max}}$ is the threshold frequency for which the absorption strength is maximal. The experimental data were measured at an electron temperature of $T_{\text{FB}} = 180 \text{ mK}$ for the four values of gate voltage, $\varepsilon$, indicated by arrows in Fig. 2a; the corresponding Kondo temperatures, $T_K(\varepsilon)$, are indicated by vertical lines in matching colours. The yellow line indicates $T_{FB}$. NRG results (solid lines), obtained using the parameters from the fit in Fig. 2a, are in remarkable agreement with experiment. Inset, the measured full (un-normalized) absorption line shape for the same $\varepsilon$ values, plotted on a linear scale. b, NRG results for $T = T_{FB}$ (solid lines) and $T = 0$ (dashed lines); the latter show the $v^{-0.5}$ behaviour expected in the strong-coupling regime, $T_{FB} \ll v \ll T_K$. c, The rescaled line shape, $A(\varepsilon)/A(T_K)$, versus $v/T_K^2$ shows a universal scaling collapse characteristic of Kondo physics.

Figure 3 | The absorption line shape $A(\varepsilon)$. a, Blue tail of $A(\varepsilon)/A(\varepsilon_{\text{max}})$ for dot 1, plotted versus the laser detuning, $ν$, on a log–log scale. Here $\varepsilon_{\text{max}}$ is the threshold frequency for which the absorption strength is maximal. The experimental data were measured at an electron temperature of $T_{\text{FB}} = 180 \text{ mK}$ for the four values of gate voltage, $\varepsilon$, indicated by arrows in Fig. 2a; the corresponding Kondo temperatures, $T_K(\varepsilon)$, are indicated by vertical lines in matching colours. The yellow line indicates $T_{FB}$. NRG results (solid lines), obtained using the parameters from the fit in Fig. 2a, are in remarkable agreement with experiment. Inset, the measured full (un-normalized) absorption line shape for the same $\varepsilon$ values, plotted on a linear scale. b, NRG results for $T = T_{FB}$ (solid lines) and $T = 0$ (dashed lines); the latter show the $v^{-0.5}$ behaviour expected in the strong-coupling regime, $T_{FB} \ll v \ll T_K$. c, The rescaled line shape, $A(\varepsilon)/A(T_K)$, versus $v/T_K^2$ shows a universal scaling collapse characteristic of Kondo physics.
\[ T_{FR} = 180 \text{ mK}, \text{ equivalent to } 15.6 \mu \text{eV} \text{ (Supplementary Information).} \]

The strong variation of the peak absorption strength and width shown in the inset of Fig. 3a is a consequence of the exponential dependence of the Kondo temperature on the gate voltage \( \varepsilon \):

\[ T_K(\varepsilon) = \sqrt{D} \exp \left[ -\left( 1 - \frac{2\varepsilon}{U_{ee}} + 1 \right)^{2} \frac{\pi U_{ee}}{8T} \right] \]  

(1)

For dot 1, \( T_K \) varies between 24 and 118 \( \mu \text{eV} \); we emphasize that even though \( T_K = 464 \mu \text{eV} \) for the black curve (Fig. 3a, inset), the dot–reservoir system is no longer in the local moment regime for this gate voltage. All line shapes carry the signatures of an optical interference effect induced by the sample structure (causing some line shapes to become negative for small red detunings), and of independently measured fluctuations in gate voltage; both effects have been taken into account in the calculated line shapes (Supplementary Information). Calculating the line shapes using NRG (solid lines) without any further fit parameters, we find remarkable agreement with experiment for all four line shapes shown in Fig. 3a, demonstrating the validity of the EAM\(^6\) for the coupled dot–reservoir system.

For blue detunings satisfying \( \nu > \max(T_{FR}, T_K) \), a perturbative description for \( A(\nu) \) is possible. The frequency scale for which the perturbative \( -\nu^{-4} \) dependence in Fig. 3a sets in and the peak absorption contrast itself strongly depend on gate voltage. Remarkably, for gate voltages such that the initial ground state is a Kondo singlet, this dependence is such that it permits a scaling collapse: Fig. 3c shows the normalized absorption line shape, \( A(\nu)/A(T_K(\varepsilon)) \), as a function of \( \nu/T_K \) for the red, green and blue curves of Fig. 3a (but omitting the black curve, which is in the mixed valence regime). We find that all three curves collapse to a universal scaling function of \( \nu/T_K \), as expected\(^4\) for the regime \( T_{FR} < \nu < U_{ee} \). Thus, the \( \varepsilon \) dependence of the crossover scale is captured by equation (1) for \( T_K \); this observation is unequivocal proof that the Kondo effect is indeed present in our system.

In the limit \( T_{FR} < \nu < T_K \), a perturbative description of the line shape is no longer valid. In the initial configuration, the exchange interaction between the quantum dot and the fermionic reservoir induces a ‘Kondo screening cloud’ that forms a singlet with the quantum dot spin. This acts as a scattering potential that induces strong phase shifts for those low-energy fermionic excitations whose energies differ from the Fermi level by \( T_K \) or less. In the final configuration after photon absorption, the quantum dot has two electrons in a local singlet state. Therefore, the Kondo screening cloud, and the scattering potential that it constitutes for reservoir electrons, disappears in the long-time limit: the corresponding ground-state wavefunction is a tensor product of the local singlet and free electronic states, with only weak phase shifts. Because the initial and final fermionic reservoir phase shifts differ (as depicted schematically in Fig. 2d), the fermionic reservoir does not remain a spectator during the \( X^- \) transition; instead, the transition matrix element between the ground states of the initial and final configurations is vanishingly small. This leads to an AOC that manifests itself by transforming a delta-function resonance (of an uncoupled quantum dot) into a power-law singularity\(^6\) of the form \( \nu^{-\gamma} \), where the exponent \( \gamma \) characterizes the extent of the AOC. For \( T_{FR} < \nu < T_K \), the absorption line shape of the \( X^- \) transition is expected to show an analogous power-law singularity. The exponent \( \gamma \) is predicted\(^23\) to range between 0 and 0.5 (assuming no magnetic field), with \( \gamma = 0.5 \) being characteristic for a Kondo-correlated initial state and an uncorrelated final state. This line shape modification is a consequence of a redistribution of the optical oscillator strength, associated with the fact that the fermionic reservoir wavefunction in the Kondo-correlated initial state has finite overlap with a range of final states consisting of electron–hole pair excitations out of a non-interacting fermionic reservoir.

If \( T_{FR} < T_K \) and the optical detuning is reduced below \( T_K \), the line shape is predicted to cross over smoothly from the perturbative \( 1/\nu \) tail to the strong-coupling \( 1/\nu^2 \) power law just discussed. This crossover is illustrated in Fig. 3b (dashed lines) by NRG calculations, performed at \( T_{FR} = 0 \) for the three \( \varepsilon \) values of Fig. 3c: Remarkably, despite drastic differences in the \( \nu > T_K \) tails due to different values of \( T_K(\varepsilon) \), all three line shapes show similar power-law exponents, of around \( \eta \approx 0.5 \), for \( \nu < T_K \). For non-zero temperature, however, the \( 1/\nu^2 \) power law is cut off and saturates once \( \nu \) decreases past \( T_{FR} \) (Fig. 3b, solid lines), because of thermal averaging over initial states with excitation energies \( \leq T_{FR} \).

A direct extraction of the \( 1/\nu^\gamma \) power law from the measured data is difficult owing to the small accessible experimental window, \( T_{FR} < \nu < T_K \). Nevertheless, we are able to determine the power-law exponent accurately for a more strongly coupled quantum dot (dot 2) by using the fact that the detailed form of the line shape sensitively depends on the exponent \( \gamma \), which can be tuned using an external magnetic field\(^6\). This tunability arises because the magnetic field, \( B_{ext} \), changes the initial dot occupancies, favouring spin up over spin down, and hence affects the overlap between the initial and final states of the transition (Supplementary Information). Figure 4a shows the \( B_{ext} = 0 \) absorption line shape for dot 2 with parameters \( U_{ee} = 7.5 \text{ meV}, I = 1 \text{ meV}, D = 6.5 \text{ meV} \) and \( U_{e\delta} = (3/2)U_{ee} \); measured at \( \nu/U_{ee} = -0.43 \) (where \( T_K = 140 \mu \text{eV} \)) and \( T_{FR} = 15.6 \mu \text{eV} \). An attempt to obtain a fit to the experimental absorption line shape using a perturbative formula\(^6\)

\[ A(\nu) \propto \frac{\nu^{T_{FR}}}{1 - e^{-\nu/T_{FR}}} \frac{\gamma}{\nu^{\gamma} + \nu^{\gamma}/4} \]

where \( \gamma \approx T_{FR} \) denotes a phenomenological relaxation rate, fails markedly for dot 2 (Fig. 4a, red curve). By striking contrast, Fig. 4b shows that an excellent fit is obtained for a weakly coupled dot (dot 3; Supplementary Information).

**Figure 4** | **Magnetic field dependence of the absorption.** a. The absorption line shape of dot 2 for \( B = 0 \) (symbols) cannot be fit by the perturbative formula (red line) given in the text. b. By contrast, for dot 3 such a fit works well. c. Absorption line shapes for dot 2, at \( B_{ext} = 0 \) and 1 T, for the blue–red trion transition. The magnetic field changes the strength of the AOC and the line shape. The small peak that appears at \( \nu = 80 \mu \text{eV} \) in the red trion absorption is due to incomplete suppression of the laser polarization that couples to the blue trion transition. Inset, the peak absorption contrast shows good agreement with the NRG calculations for \( B_{ext} \sim 1 \text{.5 T} \). d. Normalized absorption line shape for dot 2 in a log–log plot. These measurements pin the value of \( \eta(T_{FR} = 0) \to 0.5 \), which is a direct signature of a Kondo singlet in the absorption line shape. In addition, they demonstrate the tunability of an orthogonality exponent.
Figure 4c shows the magnetic field dependence of the line shape of dot 2, measured in Faraday geometry, where quantum dot optical selection rules\(^{15}\) ensure that by choosing right- or left-handed circular polarization of the laser field, it is possible to probe selectively the blue or, respectively, red trion transition that couples exclusively to the spin-up or, respectively, spin-down initial state. In comparison with the \(B_{ext} = 0\) (Fig. 4c, black squares) results, the absorption line shapes for the blue (Fig. 4c, blue dots) and red (Fig. 4c, red triangles) trion transitions at \(B_{ext} = 1\) T exhibit two striking features: the peak contrast increases (blue) or decreases (red) by a factor of \(\sim 2\), and the area under the absorption curve increases (blue) or decreases (red) by less than 20%. These observations indicate that the change in the \(B_{ext} \leq 1.5\) T line shapes is predominantly due to a line narrowing associated with an increase in the AOC power-law exponent, \(n\), of the blue trion transition and a line broadening associated with a decrease in \(n\) for the red trion transition. To quantify the field-induced change in \(n\), we plot in Fig. 4d the corresponding normalized line shapes, \(A(v)/A(T_kn)\), as functions of \(v/T_kn\) in a log–log plot, together with the corresponding NRG results (solid lines): the latter yield \(n = 0.5\) at \(B_{ext} = 0\) and \(n = 0.31\) (red trion) and \(n = 0.66\) (blue trion) at \(B_{ext} = 1\) T, proving the remarkable sensitivity of the measured line shapes to the AOC-determined power-law exponents. By contrast with Fig. 3c, the line shapes in Fig. 4d do not show a scaling collapse. We emphasize that qualitatively similar features are observed for all field values \(B_{ext} \leq 1.5\) T; for \(B_{ext} > 1.5\) T, the blue trion absorption contrast has oscillations (Fig. 4c, inset), most probably stemming from the modification of the fermionic reservoir density of states at high fields in Faraday geometry.

The area under the (un-normalized) absorption line shape is proportional to the initial occupancy, \(n_1\) or \(n_{1i}\), of the spin-up or, respectively, spin-down state. The small (\(\leq 20\%\)) field-induced change in the measured areas in Fig. 4c implies a small magnetization, \(m = (n_1 - n_{1i})/2 \approx 0.16\) (Supplementary Information). By contrast, the corresponding magnetization for a free spin would have been \(m = 0.40\). This measurement confirms that the static spin susceptibility of the initial configuration is substantially reduced relative to that of a free spin, providing yet another optical signature of the Kondo screening.

The remarkable agreement between our experimental data depicted in Figs 2–4 and the NRG calculations demonstrates Kondo correlations between a quantum dot electron and the electrons in a fermionic reservoir. The optical probe of these correlations unequivocally shows the signatures of Anderson orthogonality physics associated with the quantum quench of Kondo correlations, with field-tunable power-law exponents. Our experiments establish the potential of single, optically active quantum dots in investigating many-body physics. In addition, they pave the way for a new class of quantum optics experiments in which the influence of the simultaneous presence of non-perturbative cavity or laser coupling and Kondo correlations on electric field and photon correlations could be investigated.

METHODS SUMMARY

The InGaAs quantum dots studied in this work were grown by molecular beam epitaxy; the quantum dot layer was separated by a nominally 15-nm-thick GaAs tunnel barrier from a back gate consisting of a 40-nm-thick \(n^+\)-doped GaAs layer. This back gate serves as an electron reservoir. The distance from the quantum dot layer to the sample surface was 90 nm. A voltage applied between a 5-nm-thick tunnel barrier from a back gate consisting of a 40-nm-thick \(n^+\)-doped GaAs layer.

A.W. performed the numerical analysis. The samples were grown by S.F. C.L. and A.I.

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Key points

- Quantum dot optical selection rules allow selective probing.
- Field-induced changes in the line shapes are observed.
- The area under the absorption line is proportional to the spin-up or spin-down state.
- The experiments establish the potential of single, optically active quantum dots for many-body physics.

Supplementary Information

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